

CLAIMS

1. A dielectric ceramic composition comprising a main component including 53.00 to 80.00mol % magnesium oxide converted to MgO, 19.60 to 47.00mol % titanium oxide converted to TiO₂ and 0.05 to 0.85 mol % manganese oxide converted to MnO.
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2. The dielectric ceramic composition as in claim 1 comprising a main component including 60.00 to 70.00mol % said magnesium oxide converted to MgO, 29.60 to 39.90mol % said titanium oxide converted to TiO₂ and 0.20 to 0.60 mol % said manganese oxide converted to MnO.
- 10 3. The dielectric ceramic composition as in claim 1, as subcomponent, further comprising, with respect to entire dielectric ceramic composition, 0.00 to 0.20 mol% of at least any one of vanadium oxide, yttrium oxide, ytterbium oxide or holmium oxide converted to V₂O₅, Y₂O₃, Yb₂O₃ and Ho₂O₃ respectively.
- 15 4. The dielectric ceramic composition as in claim 3 comprising, with respect to entire dielectric ceramic composition, 0.00 to 0.05 mol% of at least any one of said vanadium oxide, yttrium oxide, ytterbium oxide or holmium oxide converted to V₂O₅, Y₂O₃, Yb₂O₃ and Ho₂O₃ respectively.
- 20 5. A process of manufacturing dielectric ceramic composition as in any of the claim 1 or 3, comprising the steps of preparing source material for said dielectric ceramic composition and firing said source material under the temperature of 1300°C or less to obtain said dielectric ceramic composition.
6. The process of manufacturing dielectric ceramic composition as in claim 5 characterized in that said source material is anneal treated after being fired in reducing atmosphere.
- 25 7. An electronic device comprising dielectric layers, characterized in that said

dielectric layers are composed of the dielectric ceramic composition as in any of claim 1 or 3.

8. An electronic device wherein inner electrodes and dielectric layers stacked alternately, characterized in that said dielectric layers are composed of the dielectric ceramic composition as in any of the claim 1 or 3.

9. The electronic device as in claim 8, wherein said internal electrode at least includes nickel.

10. A process of manufacturing electronic device as in any of claim 8 or 9, characterized in cofiring internal electrode and dielectric layers under the temperature of 1300°C or less.

11. The process of manufacturing the electronic device as in claim 8 characterized in that said dielectric ceramic composition is anneal treated after being fired in reducing atmosphere.